Lars Samuelson

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521 papers	28,885 citations	87 h-index	150 g-index
556 ext. papers	30,946 ext. citations	5.6 avg, IF	6.74 L-index

#	Paper	IF	Citations
521	InP nanowire array solar cells achieving 13.8% efficiency by exceeding the ray optics limit. *Science*, **2013**, 339, 1057-60	33.3	962
520	One-dimensional Steeplechase for Electrons Realized. *Nano Letters*, **2002**, 2, 87-89	11.5	594
519	Solid-phase diffusion mechanism for GaAs nanowire growth. *Nature Materials*, **2004**, 3, 677-81	27	593
518	Controlled polytypic and twin-plane superlattices in iii-v nanowires. *Nature Nanotechnology*, **2009**, 4, 50-5	28.7	577
517	Synthesis of branched ☐anotrees☐by controlled seeding of multiple branching events. *Nature Materials*, **2004**, 3, 380-4	27	544
516	One-dimensional heterostructures in semiconductor nanowhiskers. *Applied Physics Letters*, **2002**, 80, 1058-1060	3.4	541
515	Epitaxial III☒V Nanowires on Silicon. *Nano Letters*, **2004**, 4, 1987-1990	11.5	477
514	Structural and optical properties of high quality zinc-blende/wurtzite GaAs nanowire heterostructures. *Physical Review B*, **2009**, 80,	3.3	399
513	Nanowire resonant tunneling diodes. *Applied Physics Letters*, **2002**, 81, 4458-4460	3.4	385
512	Structural properties of B -oriented III-V nanowires. *Nature Materials*, **2006**, 5, 574-80	27	381
511	Single-electron transistors in heterostructure nanowires. *Applied Physics Letters*, **2003**, 83, 2052-2054	3.4	370
510	Controlled manipulation of nanoparticles with an atomic force microscope. *Applied Physics Letters*, **1995**, 66, 3627-3629	3.4	351
509	Nanowire Arrays Defined by Nanoimprint Lithography. *Nano Letters*, **2004**, 4, 699-702	11.5	346
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506	Optical properties of rotationally twinned InP nanowire heterostructures. *Nano Letters*, **2008**, 8, 836-41	11.5	283
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504	Failure of the vapor-liquid-solid mechanism in Au-assisted MOVPE growth of InAs nanowires. *Nano Letters*, **2005**, 5, 761-4	11.5	268
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502	Few-Electron Quantum Dots in Nanowires. *Nano Letters*, **2004**, 4, 1621-1625	11.5	253
501	Optical studies of individual InAs quantum dots in GaAs: few-particle effects. *Science*, **1998**, 280, 262-4	33.3	253
500	Gold Nanoparticles: Production, Reshaping, and Thermal Charging. *Journal of Nanoparticle Research* , **1999**, 1, 243-251	2.3	242
499	Size-, shape-, and position-controlled GaAs nano-whiskers. *Applied Physics Letters*, **2001**, 79, 3335-3337	3.4	233
498	A GaAs Nanowire Array Solar Cell With 15.3% Efficiency at 1 Sun. *IEEE Journal of Photovoltaics*, **2016**, 6, 185-190	3.7	229
497	Direct measurement of the spin-orbit interaction in a two-electron InAs nanowire quantum dot. *Physical Review Letters*, **2007**, 98, 266801	7.4	222
496	Growth and optical properties of strained GaAs-GaxIn 1-x P core-shell nanowires. *Nano Letters*, **2005**, 5, 1943-7	11.5	218
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494	Crystal phase engineering in single InAs nanowires. *Nano Letters*, **2010**, 10, 3494-9	11.5	205
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491	Monolithic GaAs/InGaP nanowire light emitting diodes on silicon. *Nanotechnology*, **2008**, 19, 305201	3.4	196
490	Au-free epitaxial growth of InAs nanowires. *Nano Letters*, **2006**, 6, 1817-21	11.5	194
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